



2N6426



# **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	12	V
I <sub>C</sub>	Collector Current - Continuous	1.2	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Мах	Units	
		2N6426		
PD	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W	

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# **NPN Darlington Transistor**

Electrical Characteristics TA = 25°C unless otherwise noted						
ymbol	Parameter	Test Conditions	Min	Мах	Units	
FF CHA	RACTERISTICS					
R)CEO	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V	
R)CBO	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	40		V	
R)EBO	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	12		V	
)	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0$		50	nA	
)	Collector Cutoff Current	$V_{CE} = 25 V, I_{B} = 0$		1.0	μΑ	
	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		50	nA	

# **ON CHARACTERISTICS\***

 $V_{(BR)CEO}$ V<sub>(BR)CBO</sub>

V<sub>(BR)EBO</sub>

 $I_{CBO}$ 

 $\mathbf{I}_{\text{CEO}}$ 

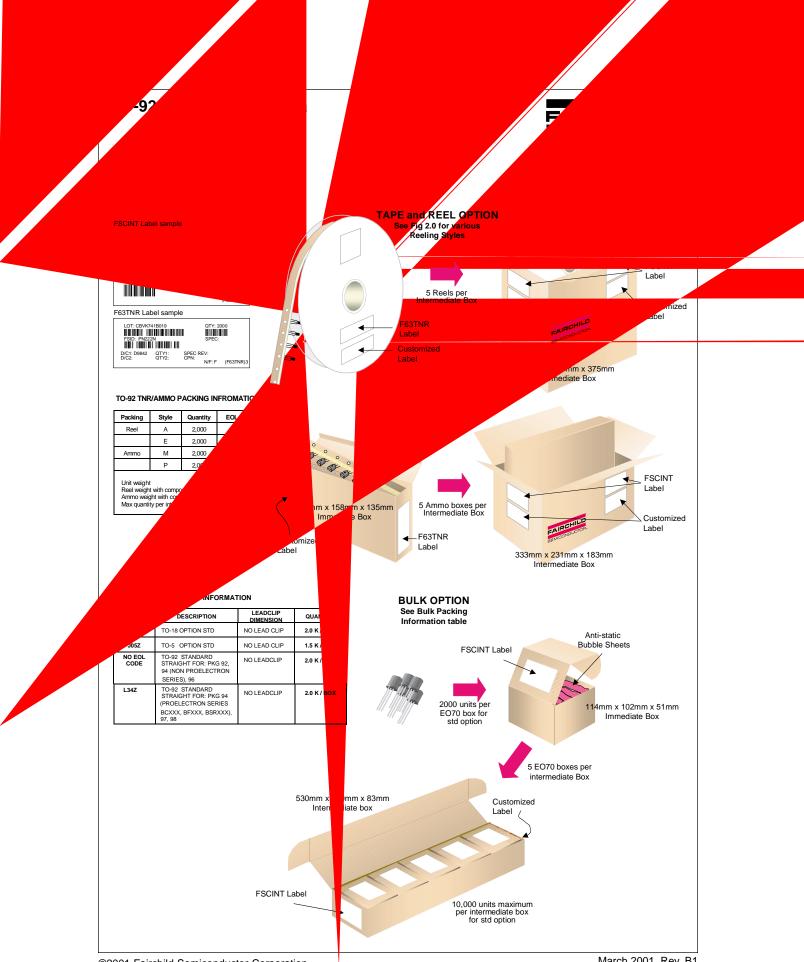
 $I_{\text{EBO}}$ 

h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	20,000	200,000	
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \text{ mA}$	30,000	300,000	
		$V_{CE} = 5.0 \text{ V}, I_{C} = 500 \text{ mA}$	20,000	200,000	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 50$ mA, $I_{\rm B} = 0.5$ mA		1.2	V
		$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		2.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{C} = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$		1.75	V

# SMALL SIGNAL CHARACTERISTICS

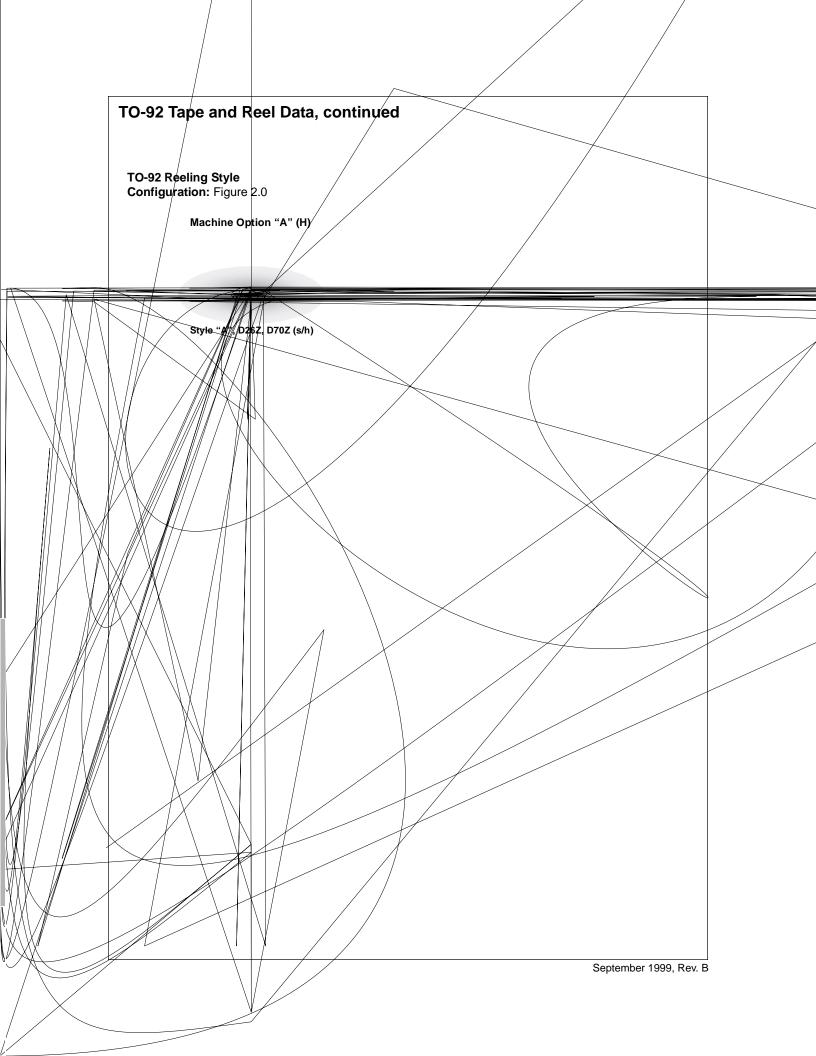
Cob	Output Capacitance	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$		7.0	pF
C <sub>ib</sub>	Input Capacitance	$V_{EB} = 1.0 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$		15	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$	20,000		
h <sub>ie</sub>	Input Impedance	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	100	2,000	kΩ
h <sub>oe</sub>	Output Admittance	f = 1.0 kHz		1,000	μmho
NF	Noise Figure	$I_{c} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $R_{s} = 100 \text{ k}\Omega,$ $f = 10 \text{ kHz to 15.7 \text{ kHz}}$		10	dB

\*Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%



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